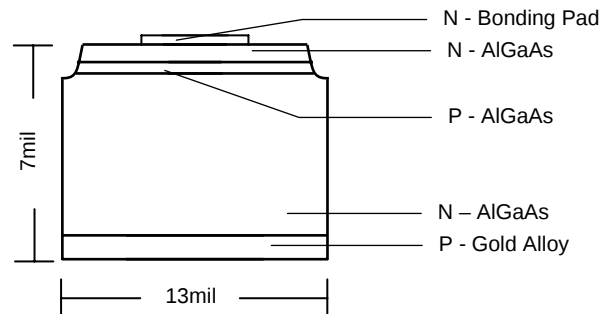
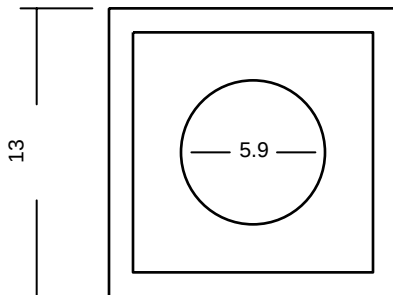


TCM660-10



❖ Outline Dimensions:



❖ Physical Structure:

Chip dimensions		Chip size	13 mil x 13 mil	330 μm x 330 μm
		Thickness	7 mil	180 μm
		Bonding pad	5.9 mil	150 μm
Electrode	Top	N (cathode)	Gold alloy	
	Backside	P (anode)	Gold alloy	

❖ Electro-Optical Characteristics:

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 20\text{mA}$	-	1.80	2.40	V
Reverse Voltage	V_R	$I_R = 10\mu\text{A}$	5	-	-	V
Peak Wavelength	λ_p	$I_F = 20\text{mA}$	650	660	670	nm
Spectral Bandwidth	$\Delta\lambda$	$I_F = 20\text{mA}$	-	25	-	nm
Radiant Flux	P_O	$I_F = 20\text{mA}$	-	1.7	-	mW
Luminous Intensity	I_v	$I_F = 20\text{mA}$	30	35	43	mcd
2 nd Peak Emission Ratio	R (λ_2/λ_p)	$I_F = 20\text{mA}$	-	0	0.1	%